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# FOR USE BY ELECTRICIANS OVERSEAS :

**最新トランジスタ規格表** (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ( $T_c=25^\circ\text{C}$ )					電気的特性 ( $T_c=25^\circ\text{C}$ )										外形	備考	
				$V_{ce0}$ (V)	$V_{be0}$ (V)	$I_c$ (mA)	$P_c$ (mW)	$T_c$ ( $^\circ\text{C}$ )	$I_{c0}$ 最大値 ( $\mu\text{A}$ )	直流又はパルス $h_{FE}$		バイアス		$h_{FE}$	$h_{ie}$	$h_{re}$	$h_{oe}$	$f_{\alpha b}$			$C_{ob}$
				$V_{ce}$ (V)	$I_c$ (mA)	$V_{ce}$ (V)	$I_c$ (mA)	$V_{ce}$ (V)	$I_c$ (mA)	$h_{FE}$ *	$h_{ie}$ ( $\Omega$ )	$h_{re}$ ( $\times 10^{-4}$ )	$h_{oe}$ ( $\mu\text{S}$ )	$f_{\alpha b}$ (Mc)	$C_{ob}$ (pF)	$r_{bb'}$ ( $\Omega$ )					
1	2	3	4	5					6		7			8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6  $I_{cB0}$  MAXIMUM VALUE AND  $V_{cB}$  VALUE (CRITERIA FOR MEASURING  $I_{cB0}$ )
- 7 STANDARD VALUE OF DC/PULSE  $h_{FE}$  AND  $V_{cE}$ ,  $I_c$  (CRITERIA FOR MEASURING DC/PULSE  $h_{FE}$ )
- 8 STANDARD VALUE OF  $h$  PARAMETERS AND BIAS  $V_{cB}$ ,  $I_E$  (CRITERIA FOR MEASURING  $h$  PARAMETERS)

- \* INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
  - 9  $f_{\alpha b}$  OF RF CHARACTERISTIC, EXCEPT IN CASE OF \* WHICH INDICATES VALUE OF  $f_T$ .
  - 10  $C_{ob}$  AND  $r_{bb'}$  OF RF CHARACTERISTICS EXCEPT IN CASE OF \* IN  $r_{bb'}$  COLUMN WHICH INDICATES VALUE OF  $h_{ie}$  (real)
  - 11 OUTLINE
  - 12 REMARKS
- : とコンプリ : COMPLEMENTARY TO .....

型名	社名	用途	構造	最大定格 (T <sub>a</sub> = 25°C)					電 気 的 特 性 (T <sub>a</sub> = 25°C)										外形	備考			
				V <sub>CB0</sub> (V)	V <sub>EBO</sub> (V)	I <sub>C</sub> (mA)	P <sub>C</sub> (mW)	T <sub>J</sub> (°C)	I <sub>CB0</sub> 最大値 (μA)	V <sub>CB(V)</sub>	直流又はパルス h <sub>FE</sub> V <sub>CE(V)</sub>	バイアス I <sub>C(mA)</sub>	V <sub>CB(V)</sub>	I <sub>E(mA)</sub>	h <sub>fe</sub> h <sub>fe</sub> *	h <sub>ie</sub> h <sub>ie</sub> * (Ω)	h <sub>re</sub> h <sub>re</sub> * (×10 <sup>-4</sup> )	h <sub>oe</sub> h <sub>oe</sub> * (μΩ)			f <sub>αβ</sub> f <sub>T</sub> * (Mc)	C <sub>ob</sub> (pF)	f <sub>βh</sub> h <sub>βh</sub> (real)* (Ω)
★ 2SC1181	三洋	RF	Si.EP	40	3	50	300	125	1	35	15~120	6	1	6	-1			400*	C <sub>rr1</sub>				
" 1182	"	"	"	25	3	50	300	125	1	20	15~120	6	1	6	-1			400*	C <sub>rr1</sub>				
" 1183																							
★ " 1184	日電	SW	Si.TMe	900	5	1A	50W (T <sub>c</sub> =25°C)	150	500	800	60	10	200									102	
" 1185	"	"	"	300	5	700	50W (T <sub>c</sub> =25°C)	150	100	200	90	10	400									102	
" 1186																							
" 1187	日電	RF	Si.P	40	4	25	250	125	0.1	20	90	10	3	10	-3			700*	0.4	C <sub>c</sub> f <sub>βh</sub> 12pS	138C	フォワード AGC	
" 1188	"	"	Si.E	40	4	30	250	125	0.1	20	90	10	10	10	-10			850*	0.5	C <sub>c</sub> f <sub>βh</sub> 9pS	138C		
" 1189	"	"	"	50	4	30	250	125	0.1	20	90	10	10	10	-10			850*	0.5	C <sub>c</sub> f <sub>βh</sub> 9pS	138C		
" 1190	松下	PA	Si.EP	36	4	2.5A	30W (T <sub>c</sub> =25°C)	175	100	20	50	13.5	400					600*	17			142	
" 1191	"	"	"	36	4	3.5A	45W (T <sub>c</sub> =25°C)	175	0.5mA	20	50	13.5	800						50			143	
" 1192	"	"	"	36	4	5A	60W (T <sub>c</sub> =25°C)	175	1mA	20	60	13.5	1A						350*	100		143	
" 1193	東芝	LN	"	20	2	30	200	175	0.1	10	70	10	10	10	-10			4500*	0.8	20*		140	
" 1194																							
" 1195	東芝	PA.SW	Si.T	200	5	2.5A	100W (T <sub>c</sub> =25°C)	150	10	200	30~150	5	1A									102	
" 1196	"	PA	Si.EP	60	4.5	750	10W (T <sub>c</sub> =25°C)	175	5	15	50	10	1A	10	-150			800*	5			135	
" 1197	"	"	"	60	4.5	2A	30W (T <sub>c</sub> =25°C)	175	10	15	55	10	1A	10	-150			700*	<25			135	
★ " 1198	"	"	"	45	4	3.5A	30W (T <sub>c</sub> =25°C)	175	50	15	>20	10	1A	10	-150			800*	30			213	
" 1199	"	RF.LN	"	50	3	300	600	150	0.1	20	80	10	20	10	-20			1400*	2.2	C <sub>c</sub> f <sub>βh</sub> 5pS		85B	
" 1200	"	PA	"	40	3.5	180	2.5W (T <sub>c</sub> =25°C)	175	1	20	120	5	100	5	-100			1700*	2.3			136	
" 1201																							
" 1202																							
" 1203																							
★ " 1204	H立	RF.AF	Si.EP	30		100	310	125	0.5	18	250	12	2	12	-0.1	130	16.5k	0.7	11	230*	1.8	60*	37A
★ " 1205	"	RF.Mix Conv. Osc	Si.P	30		100	310	125	0.5	18	120	12	2	12	-2					230*	1.5	C <sub>c</sub> f <sub>βh</sub> 13pS	37A
★ " 1206	三菱	RF.PA	Si.EP	45	4.5	1.7A	25W (T <sub>c</sub> =25°C)	175	1mA	30	50	25	50										209
★ " 1207	"	"	"	45	4.5	3A	30W (T <sub>c</sub> =25°C)	175	2mA	30	50	25	50										209
" 1208	"	"	"	36	5	10A	60W (T <sub>c</sub> =25°C)	175	2mA	15	50	10	500										127
" 1209	"	"	"	25	4	700	500	125	1	25	100	1	500	6	-10			150*	15	C <sub>c</sub> f <sub>βh</sub> 100pS	138B	2SA695 とコンプアリ	
" 1210	"	"	"	45	4	500	500	125	1	25	100	2	150	6	-10			130*	10	C <sub>c</sub> f <sub>βh</sub> 100pS	138B	2SA696 とコンプアリ	